



PJD16N06A

60V N-Channel Enhancement Mode MOSFET

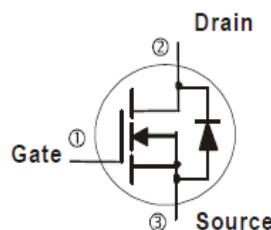
Voltage 60 V Current 16 A

Features

- $R_{DS(ON)}$, $V_{GS} @ 10V, I_D @ 8A < 50m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ 4.5V, I_D @ 4A < 60m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.
(Halogen Free)

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current <small>$T_C=25^\circ C$</small>	I_D	16	A
		10	
Pulsed Drain Current ^(Note 1)	I_{DM}	64	
Power Dissipation <small>$T_C=25^\circ C$</small>	P_D	27	W
		10.8	
Continuous Drain Current <small>$T_A=25^\circ C$</small>	I_D	4.4	A
		3.5	
Power Dissipation	P_D	2.0	W
Power Dissipation		1.3	
Single Pulse Avalanche Energy ^(Note 6)	E_{AS}	11	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	°C
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{\theta JC}$	°C/W
	Junction to Ambient	$R_{\theta JA}$	

- Limited only By Maximum Junction Temperature



PJD16N06A

Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.77	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$	-	37	50	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$	-	42	60	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=4A,$ $V_{GS}=10V$ (Note 1,2)	-	14	-	nC
Gate-Source Charge	Q_{gs}		-	2.9	-	
Gate-Drain Charge	Q_{gd}		-	2.3	-	
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	815	-	pF
Output Capacitance	C_{oss}		-	379	-	
Reverse Transfer Capacitance	C_{rss}		-	110	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=1A,$ $V_{GS}=10V, R_G=3.3\Omega$ (Note 1,2)	-	3.9	-	ns
Turn-On Rise Time	t_r		-	13	-	
Turn-Off Delay Time	$t_{d(off)}$		-	23	-	
Turn-Off Fall Time	t_f		-	6.7	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	16	A
Diode Forward Voltage	V_{SD}	$I_S=1A, V_{GS}=0V$	-	0.73	1.0	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_J(MAX)=150^\circ C$. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^\circ C$.
4. The maximum current rating is package limited.
5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. The test condition is $L=0.1mH, I_{AS}=15A, V_{DD}=25V, V_{GS}=10V$
7. Guaranteed by design, not subject to production testing.



PJD16N06A

TYPICAL CHARACTERISTIC CURVES

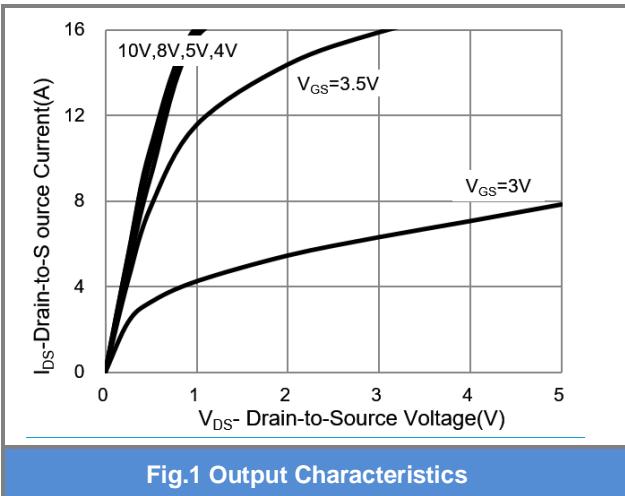


Fig.1 Output Characteristics

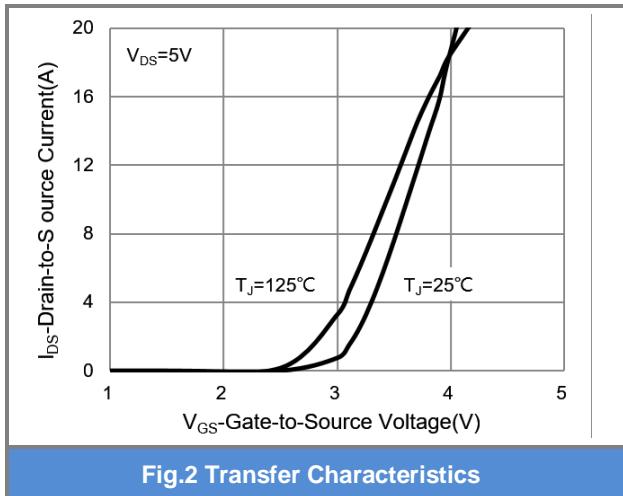


Fig.2 Transfer Characteristics

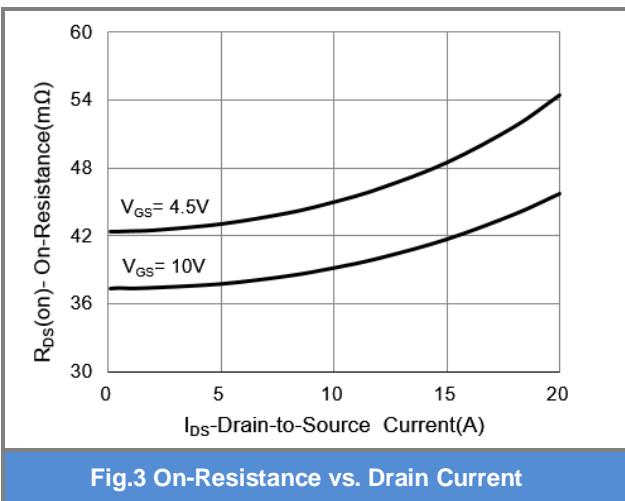


Fig.3 On-Resistance vs. Drain Current

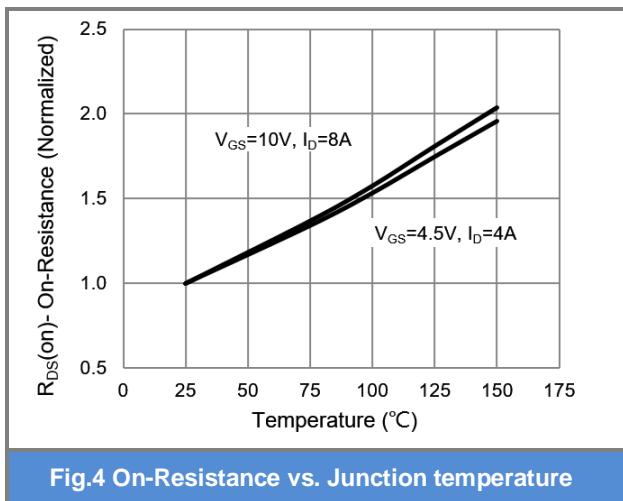


Fig.4 On-Resistance vs. Junction temperature

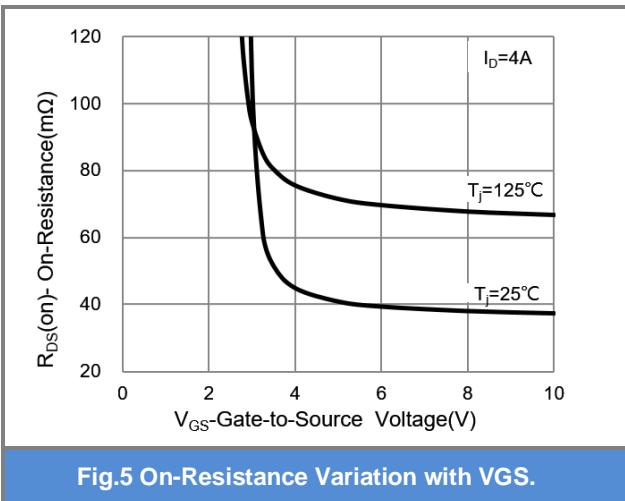


Fig.5 On-Resistance Variation with VGS.

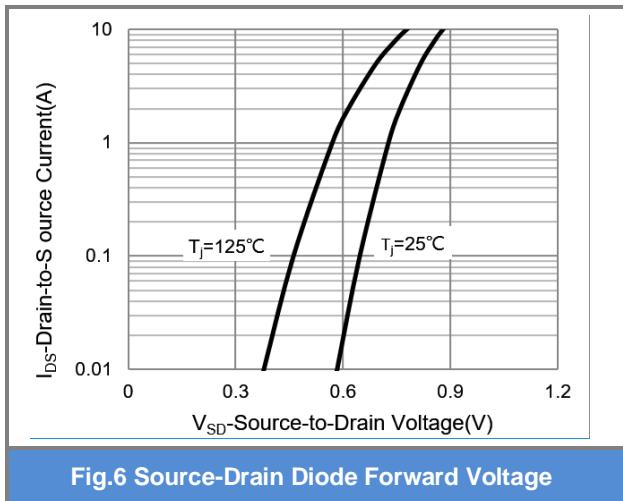


Fig.6 Source-Drain Diode Forward Voltage



PJD16N06A

TYPICAL CHARACTERISTIC CURVES

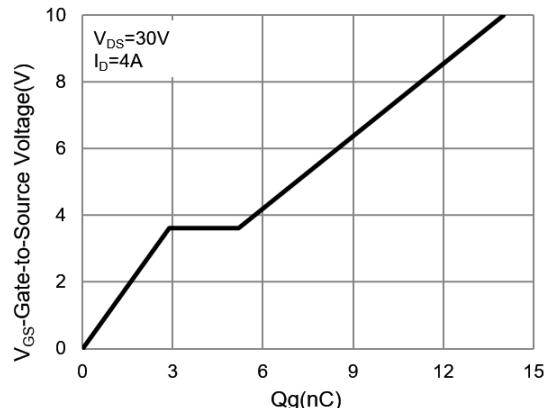


Fig.7 Gate-Charge Characteristics

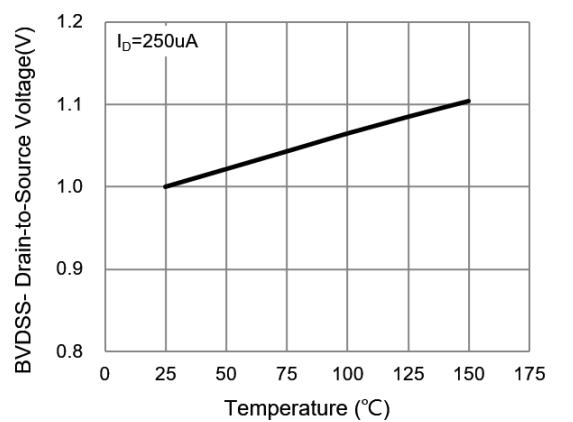


Fig.8 Breakdown Voltage Variation vs. Temperature

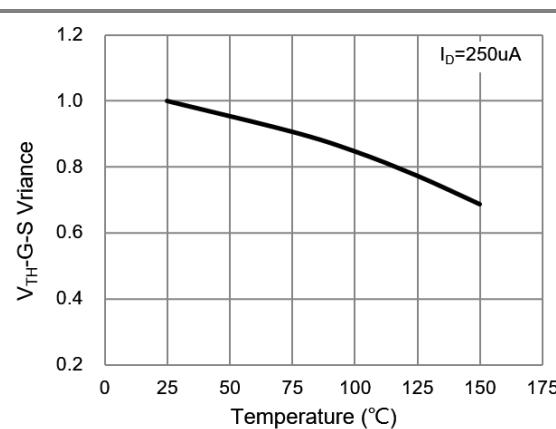


Fig.9 Threshold Voltage Variation with Temperature

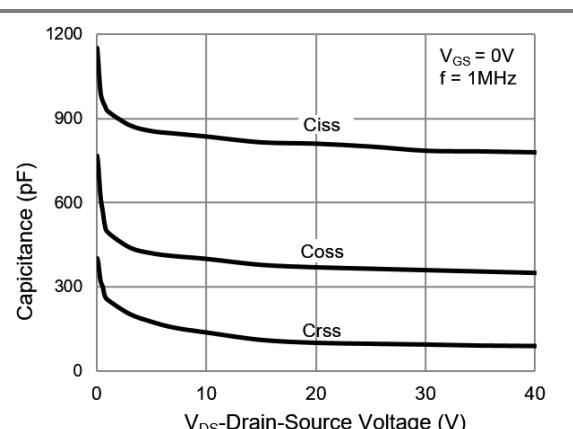


Fig.10 Capacitance vs. Drain-Source Voltage

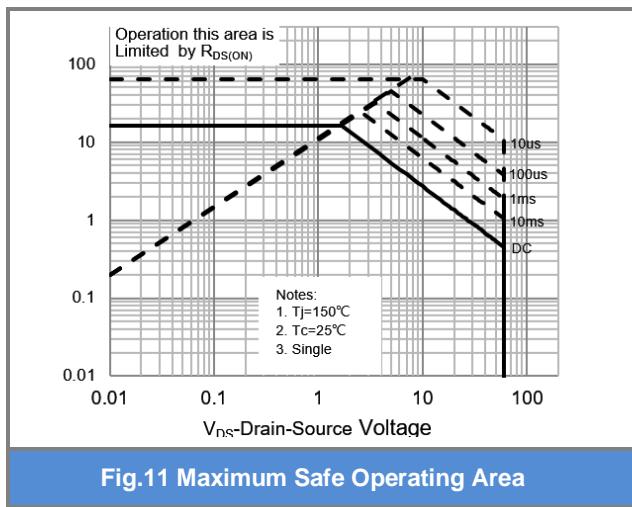


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

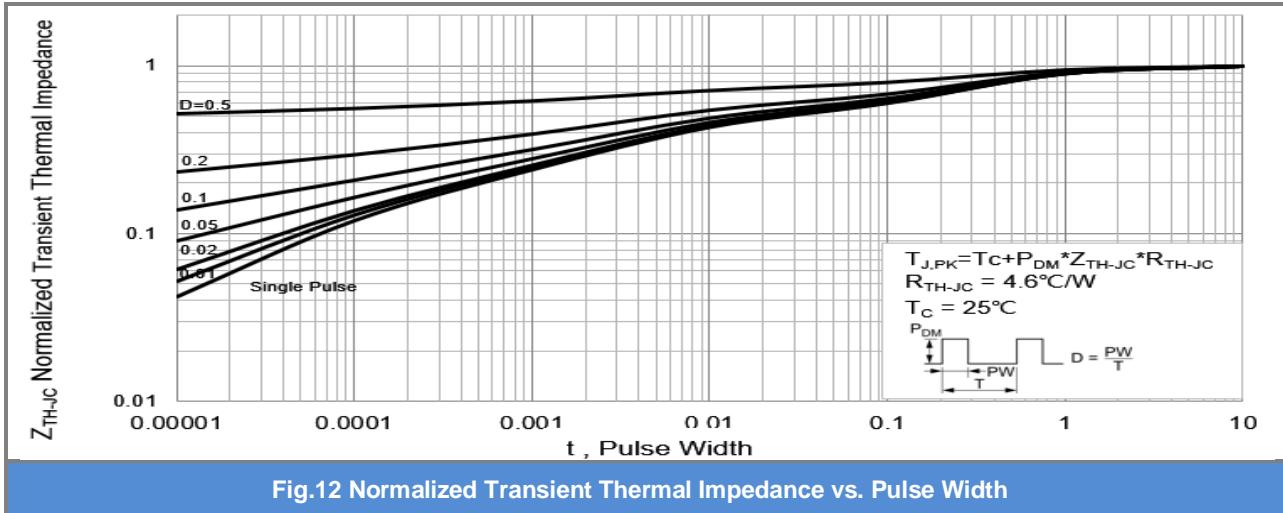
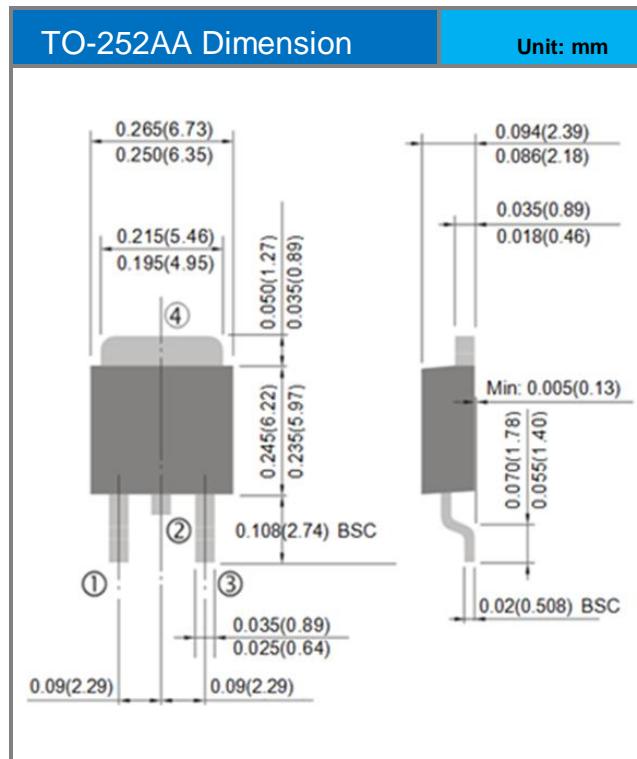


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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Packaging Information



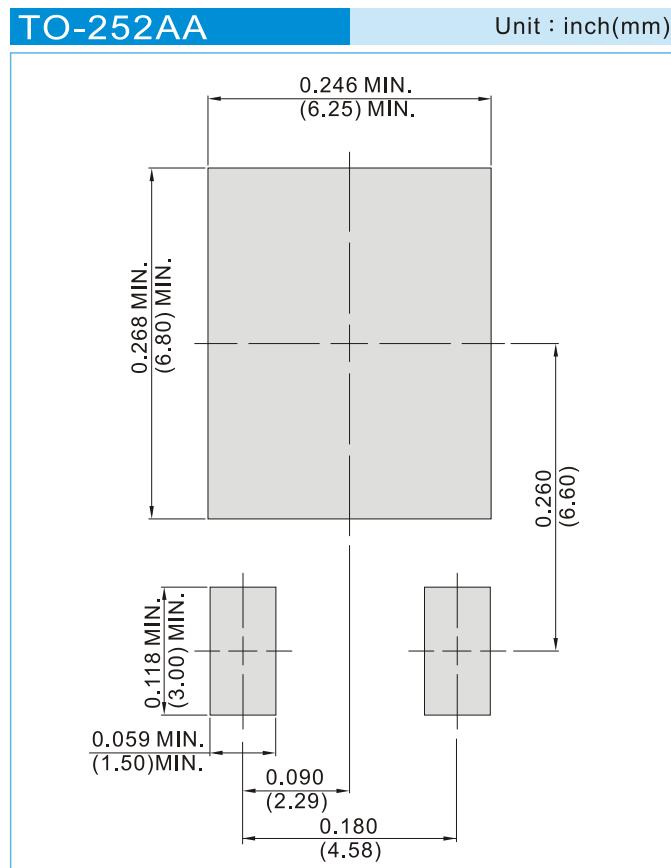


PJD16N06A

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD16N06A_L2_00001	TO-252AA	3,000pcs / 13" reel	D16N06A	Halogen free

MOUNTING PAD LAYOUT





PJD16N06A

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